# **High Voltage Transistors NPN Silicon**

MMBT5550L, MMBT5551L

#### **Features**

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage  MMBT5550  MMBT5551	V <sub>CEO</sub>	140 160	Vdc
Collector – Base Voltage MMBT5550 MMBT5551	V <sub>CBO</sub>	160 180	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	600	mAdc
Electrostatic Discharge Human Body Model Machine Model	ESD	> 8000 > 400	<b>V</b>

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T <sub>A</sub> = 25°C Derate Above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) @T <sub>A</sub> = 25°C Derate Above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

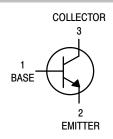
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

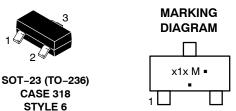
- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



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x1x = Device Code

M1F = MMBT5550LT

G1 = MMBT5551LT

M = Date Code\*

■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBT5550LT1G, NSVMMBT5550LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5550LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT5551LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT5551LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5551LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBT5551LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 3) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MMBT5550 MMBT5551	V <sub>(BR)CEO</sub>	140 160	- -	Vdc
Collector – Base Breakdown Voltage ( $I_C = 100 \mu Adc, I_E = 0$ )	MMBT5550 MMBT5551	V <sub>(BR)</sub> CBO	160 180	- -	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)		V <sub>(BR)EBO</sub>	6.0	-	Vdc
Collector Cutoff Current	MMBT5550 MMBT5551 MMBT5550 MMBT5551	I <sub>CBO</sub>	- - -	100 50 100 50	nAdc μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 4.0 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	-	50	nAdc
ON CHARACTERISTICS					
DC Current Gain $(I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ $(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ $(I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT5550 MMBT5551 MMBT5550 MMBT5551 MMBT5550 MMBT5551	h <sub>FE</sub>	60 80 60 80 20 30	- 250 250 - -	-
Collector – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )	Both Types MMBT5550 MMBT5551	V <sub>CE(sat)</sub>	- - -	0.15 0.25 0.20	Vdc
Base – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )	Both Types MMBT5550 MMBT5551	V <sub>BE(sat)</sub>	- - -	1.0 1.2 1.0	Vdc
Collector Emitter Cut-off (V <sub>CB</sub> = 10 V) (V <sub>CB</sub> = 75 V)	Both Types	I <sub>CES</sub>	- -	50 100	nA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 µs, Duty Cycle = 2.0%.

#### **TYPICAL CHARACTERISTICS**

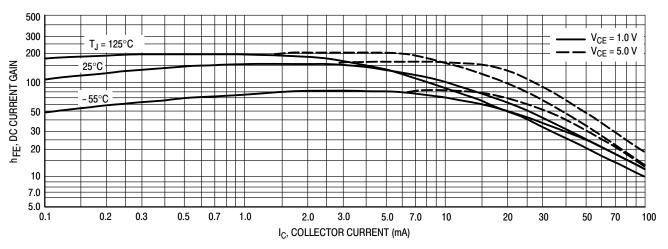


Figure 1. DC Current Gain

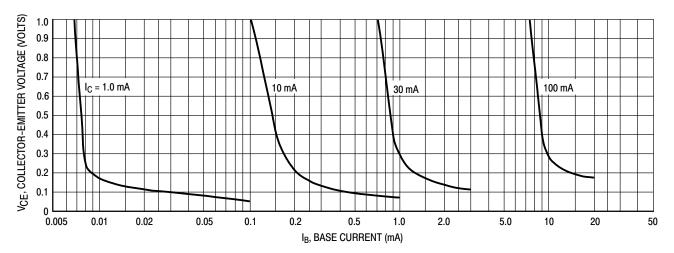


Figure 2. Collector Saturation Region

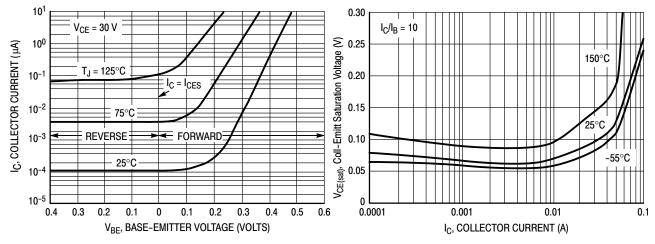
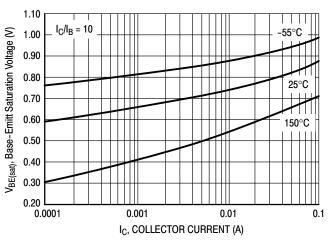


Figure 3. Collector Cut-Off Region

Figure 4. V<sub>CE(sat)</sub>

#### **TYPICAL CHARACTERISTICS**



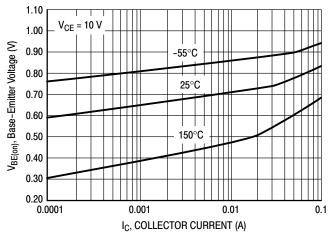
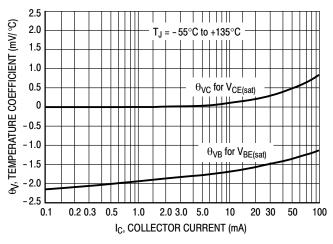


Figure 5. V<sub>BE(sat)</sub>

Figure 6. V<sub>BE(on)</sub>



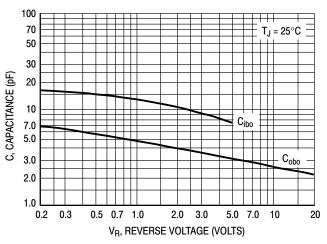
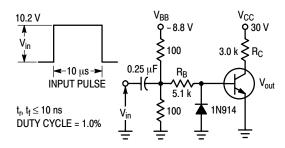


Figure 7. Temperature Coefficients

Figure 8. Capacitances



Values Shown are for I<sub>C</sub> @ 10 mA

Figure 9. Switching Time Test Circuit

#### **TYPICAL CHARACTERISTICS**

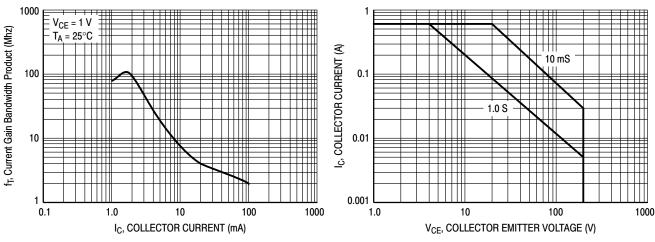


Figure 10. Current Gain Bandwidth Product



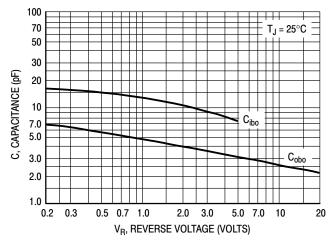


Figure 12. Capacitances

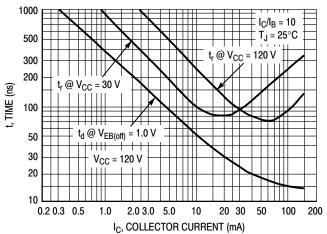


Figure 13. Turn-On Time



SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b **TOP VIEW**







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

3. ANODE

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		10°	O۰		10°

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE		PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE		2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE		3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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